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Kind regards,

Team Nexperia

Low capacitance 6-fold ESD protection diode arrays

Rev. 03 — 18 August 2009

Product data sheet

1. Product profile

1.1 General description

Low capacitance 6-fold ESD protection diode arrays in small plastic packages designed to protect up to six transmission or data lines from the damage caused by ElectroStatic Discharge (ESD) and other transients.

Table 1. Product overview

Type number	Package							
	Name	NXP						
PESD5V0L6UAS	TSSOP8	SOT505-1						
PESD5V0L6US	SO8	SOT96-1						

1.2 Features

- ESD protection of up to six lines
- Low diode capacitance
- Max. peak pulse power: P_{PP} = 35 W
- Low clamping voltage: V_{(CL)R} = 15 V
- Ultra low leakage current: I_{RM} = 8 nA
- ESD protection of up to 20 kV
- IEC 61000-4-2, level 4 (ESD)
- IEC 61000-4-5 (surge); I_{PP} = 2.5 A

1.3 Applications

- Computers and peripherals
- Communication systems
- Audio and video equipment
- High speed data lines
- Parallel ports

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{RWM}	reverse stand-off voltage		-	-	5	V
C_d	diode capacitance	$V_R = 0 V;$ f = 1 MHz	-	16	19	pF



Low capacitance 6-fold ESD protection diode arrays

2. Pinning information

Table 3. Discrete pinning

Table 6.	Discrete pinning		
Pin	Description	Simplified outline	Symbol
TSSOP8			
1	cathode 1		
2	cathode 2	8	1 8
3	cathode 3		2 7 7
4	cathode 4		
5	cathode 5		3 6
6	common anode	1 - 1 - 1 - 4	4 4 5
7	common anode		
8	cathode 6		sym004
SO8			
1	cathode 1		
2	cathode 2	8	1 8
3	cathode 3		2 7
4	cathode 4		
5	cathode 5	1 1 1 1 1 1 4	3 6
6	common anode		4 4 5
7	common anode		
8	cathode 6		sym004

3. Ordering information

Table 4. Ordering information

· · · · · · · · · · · · · · · · · · ·											
Type number	Package										
	Name	ne Description									
PESD5V0L6UAS	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm	SOT505-1								
PESD5V0L6US	SO8	plastic small outline package; 8 leads; body width 3.9 mm	SOT96-1								

4. Marking

Table 5. Marking

Type number	Marking code
PESD5V0L6UAS	5V06U
PESD5V0L6US	5V06US

Low capacitance 6-fold ESD protection diode arrays

Limiting values 5.

Table 6. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per diode					
P_{PP}	peak pulse power	8/20 μs pulse	[1][2]	35	W
I_{PP}	peak pulse current	8/20 μs pulse	[1][2]	2.5	Α
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Non-repetitive current pulse 8/20 µs exponentially decay waveform according to IEC 61000-4-5; see Figure 1.

Table 7. **ESD** maximum ratings

Symbol	Parameter	Conditions	Min	Max	Unit
ESD	electrostatic discharge capability	IEC 61000-4-2 (contact discharge)	[1][2]	20	kV
		HBM MIL-STD883	-	10	kV

^[1] Device stressed with ten non-repetitive ElectroStatic Discharge (ESD) pulses; see Figure 2.

Table 8. **ESD** standards compliance

Standard	Conditions
IEC 61000-4-2, level 4 (ESD); see Figure 2	> 15 kV (air); > 8 kV (contact)
HBM MIL-STD883, class 3	> 4 kV

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^[2] Measured from pin 1, 2, 3, 4, 5 or 8 to pin 6 or 7.

^[2] Measured from pin 1, 2, 3, 4, 5 or 8 to pin 6 or 7.

Low capacitance 6-fold ESD protection diode arrays

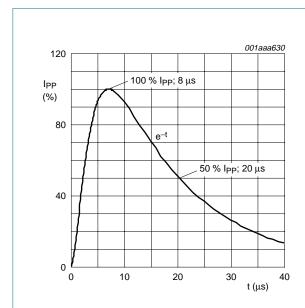


Fig 1. 8/20 μs pulse waveform according to IEC 61000-4-5

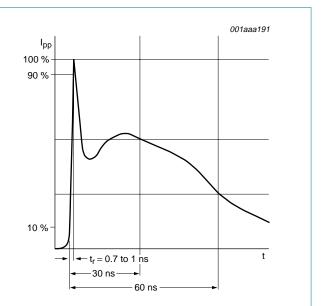


Fig 2. ElectroStatic Discharge (ESD) pulse waveform according to IEC 61000-4-2

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Low capacitance 6-fold ESD protection diode arrays

Characteristics

Table 9. **Characteristics**

T_{amb} = 25 °C unless otherwise specified

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per diode							
V_{RWM}	reverse stand-off voltage			-	-	5	V
I _{RM}	reverse leakage current	$V_{RWM} = 5 V$		-	8	25	nA
$V_{(CL)R}$	clamping voltage	$I_{PP} = 1 A$	[1][2]	-	-	10	V
		$I_{PP} = 2.5 A$	[1][2]	-	-	15	V
V _(BR)	breakdown voltage	$I_R = 1 \text{ mA}$		6.4	6.8	7.2	V
r _{dif}	differential resistance	$I_R = 1 \text{ mA}$		-	-	100	Ω
C_d	diode capacitance	$V_R = 0 V$; $f = 1 MHz$; see Figure 5		-	16	19	pF

^[1] Non-repetitive current pulse 8/20 μs exponentially decay waveform according to IEC 61000-4-5; see Figure 1.

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^[2] Measured between each cathode on pins 1, 2, 3, 4, 5 or 8 and anode on pin 6 or 7.

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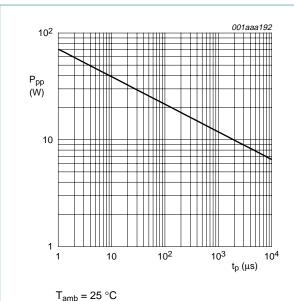


Fig 3. Peak pulse power as a function of exponential pulse duration t_p; typical values

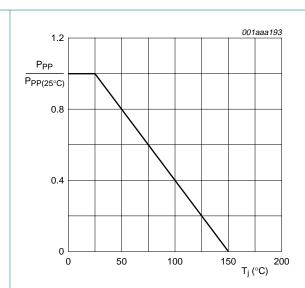


Fig 4. Relative variation of peak pulse power as a function of junction temperature; typical values

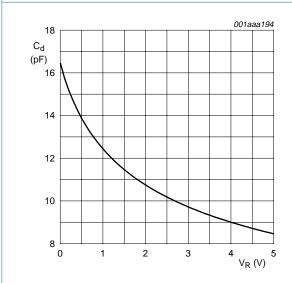


Fig 5. Diode capacitance as a function of reverse voltage; typical values

 $T_{amb} = 25 \, ^{\circ}C; f = 1 \, MHz$

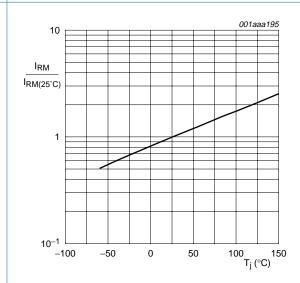
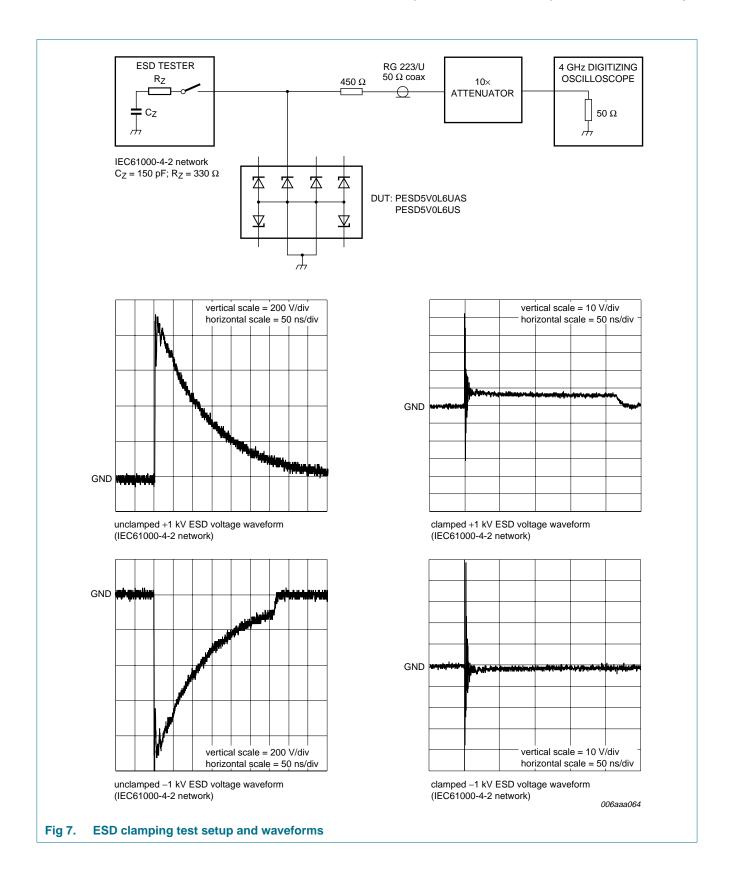


Fig 6. Relative variation of reverse leakage current as a function of junction temperature; typical values

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Low capacitance 6-fold ESD protection diode arrays

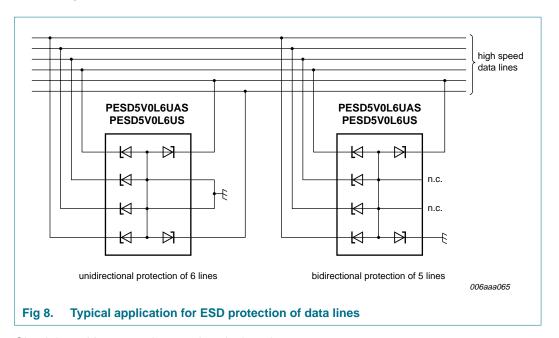


Low capacitance 6-fold ESD protection diode arrays

7. Application information

The PESD5V0L6UAS and the PESD5V0L6US are designed for protection of up to six unidirectional data lines from the damage caused by ElectroStatic Discharge (ESD) and surge pulses. The PESD5V0L6UAS and the PESD5V0L6US may be used on lines where the signal polarity is above or below ground.

The PESD5V0L6UAS and the PESD5V0L6US provide a surge capability of 35 W per line for a $8/20~\mu s$ waveform.



Circuit board layout and protection device placement:

Circuit board layout is critical for the suppression of ESD, EFT and surge transients. The following guidelines are recommended:

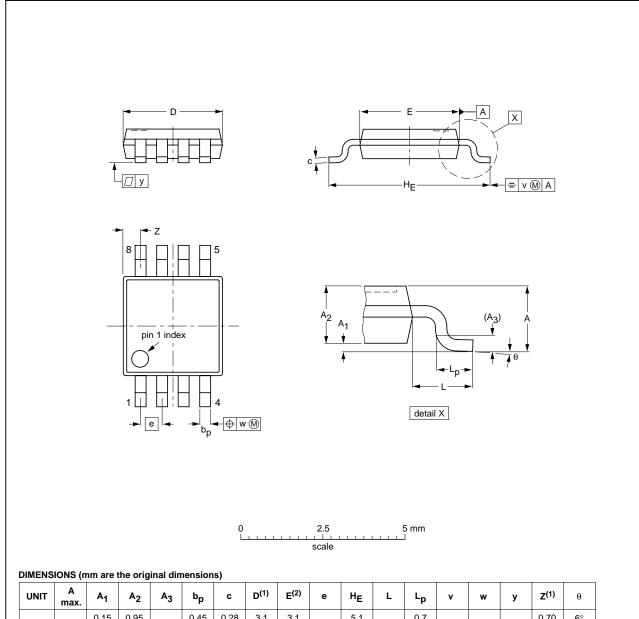
- 1. Place the protection device as close to the input terminal or connector as possible.
- The path length between the protection device and the protected line should be minimized.
- 3. Keep parallel signal paths to a minimum.
- 4. Avoid running protection conductors in parallel with unprotected conductor.
- 5. Minimize all printed-circuit board conductive loops including power and ground loops.
- 6. Minimize the length of the transient return path to ground.
- 7. Avoid using shared transient return paths to a common ground point.
- 8. Ground planes should be used whenever possible. For multilayer printed-circuit boards, use ground vias.

Low capacitance 6-fold ESD protection diode arrays

Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm

SOT505-1



UNIT	A max.	A ₁	A ₂	А3	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	v	w	у	Z ⁽¹⁾	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.45 0.25	0.28 0.15	3.1 2.9	3.1 2.9	0.65	5.1 4.7	0.94	0.7 0.4	0.1	0.1	0.1	0.70 0.35	6° 0°

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

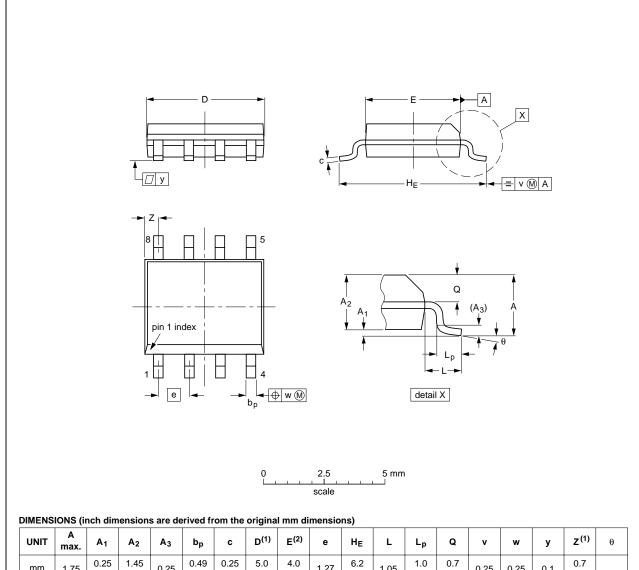
VERSION IEC JEDEC JEITA PRO		
	PROJECTION	ISSUE DATE
SOT505-1		99-04-09 03-02-18

Package outline SOT505-1 (TSSOP8) Fig 9.

Low capacitance 6-fold ESD protection diode arrays

SO8: plastic small outline package; 8 leads; body width 3.9 mm

SOT96-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	5.0 4.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01		0.0100 0.0075	0.20 0.19	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	0°

Notes

Product data sheet

- 1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT96-1	076E03	MS-012				99-12-27 03-02-18
	•	•	·			

Fig 10. Package outline SOT96-1 (SO8/MS-012)

Low capacitance 6-fold ESD protection diode arrays

Packing information

Table 10. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			1000	2500
PESD5V0L6UAS	SOT505-1	8 mm pitch, 12 mm tape and reel	-	-118
PESD5V0L6US	SOT96-1	8 mm pitch, 12 mm tape and reel	-115	-118

^[1] For further information and the availability of packing methods, see $\underline{\text{Section 12}}$.

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10. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PESD5V06UAS_US_3	20090818	Product data sheet	-	PESD5V06UAS_US_2
Modifications: • This data sheet was changed to re including new legal definitions and content. • Table 3 "Discrete pinning": amend				
PESD5V06UAS_US_2	20041109	Product data sheet	-	PESD5V0L6US_1
PESD5V0L6US_1	20040315	Product specification	-	-

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11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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NXP Semiconductors

PESD5V0L6UAS; PESD5V0L6US

Low capacitance 6-fold ESD protection diode arrays

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